# VS-HFA08TA60CS-M3

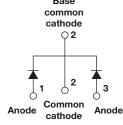
Vishay Semiconductors

## **HEXFRED**<sup>®</sup> Ultrafast Soft Recovery Diode, 2 x 4 A



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Base



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub> 8 A						
V <sub>R</sub>	600 V					
V <sub>F</sub> at I <sub>F</sub>	2.2 V					
t <sub>rr</sub> (typ.)	17 ns					
T <sub>J</sub> max.	150 °C					
Package	D <sup>2</sup> PAK (TO-263AB)					
Circuit configuration	Common cathode					

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Specified at operating conditions
- HALOGEN Meets MSL level 1, per J-STD-020, LF maximum FREE peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### DESCRIPTION

VS-HFA08TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the VS-HFA08TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward current	- I <sub>F</sub>	T <sub>C</sub> = 100 °C	4			
per device			8	А		
Single pulse forward current	I <sub>FSM</sub>		25	A		
Maximum repetitive forward current	I <sub>FRM</sub>		16			
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	25	W		
		T <sub>C</sub> = 100 °C	10	۷V		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-		
Maximum forward voltage		I <sub>F</sub> = 4.0 A		-	1.5	1.8	V	
	V <sub>FM</sub>	I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2		
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7		
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	See fig. 0	-	0.17	3.0		
leakage current	I <sub>RM</sub>	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	44	300	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V See fig. 3		-	4.0	8.0	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from pa	Measured lead to lead 5 mm from package body - 8.0 -				nH	

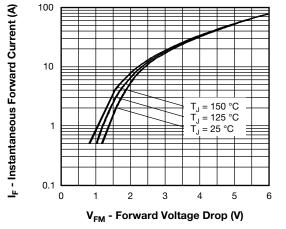
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \ dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	17	-	ns	
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 4.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	38	57		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	A nC	
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	3.7	6.7		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	40	60		
See fig. 9 and 10 Peak rate of fall of recovery current during $t_b$ See fig. 11 and 12	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	70	105		
	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	A /	
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	A∕µs	

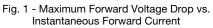
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0	K/W		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	R <sub>thJA</sub> Typical socket mount		-	80			
Maight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	HFA08TA60CS					

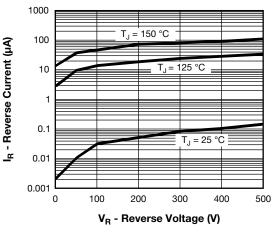


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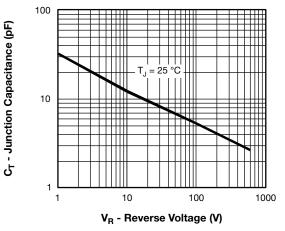


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

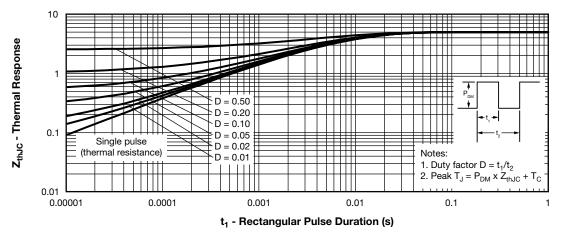
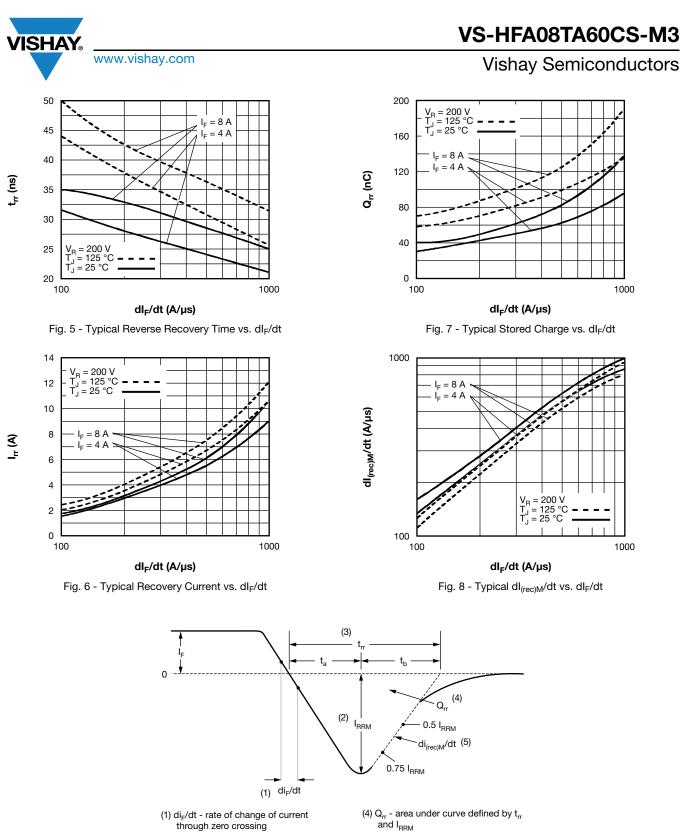
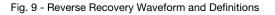


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



- (2) I<sub>BBM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- $\Omega = \frac{t_{rr} \times I_{RRM}}{t_{rr} \times I_{RRM}}$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 



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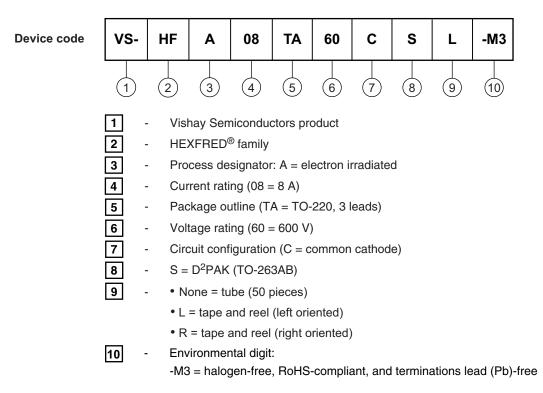
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**ORDERING INFORMATION TABLE** 

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ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA08TA60CS-M3	50	1000	Antistatic plastic tube					
VS-HFA08TA60CSR-M3	800	800	13" diameter reel					
VS-HFA08TA60CSL-M3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

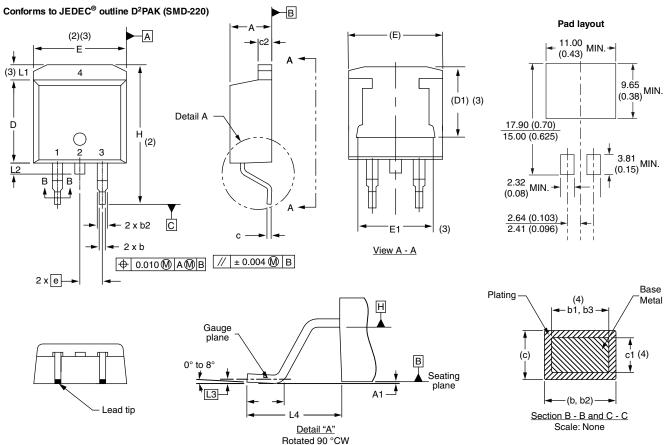
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D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches

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<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL		MILLIM	ETERS	INC	HES	NOTES
	STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54	2.54 BSC		BSC	
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25 BSC		0.010	BSC	
	L4	4.78	5.28	0.188	0.208	

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#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

Controlling dimension: inches (6)

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

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